

PATENT
8013-1139

IN THE U.S. PATENT AND TRADEMARK OFFICE

In re application of

YAMAGUCHI et al.

Conf. 1202

Application No. 09/944,186

Group 2811

Filed September 4, 2001

Examiner Shouxiang Hu

NITRIDE BASED SEMICONDUCTOR LIGHT-EMITTING DEVICE

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

In compliance with Rules 1.97 and 1.98, and in fulfillment of the duty of disclosure under Rule 1.56, the accompanying documents, copies of which are attached to this statement, are made of record on the enclosed Form PTO-1449.

A concise explanation of the relevance of these items is that these references were cited by the European Patent Office in the corresponding European Application Serial No. EP 01 12 0692. A copy of the European Search Report in which they were cited is attached hereto.

Under the provisions of 37 CFR 1.97(e), the undersigned hereby certifies that each item of information contained in this Information Disclosure Statement was first cited in any communication from a foreign Patent Office in a

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counterpart foreign application not more than three months prior to the filing of this Statement.

Respectfully submitted,

YOUNG & THOMPSON

A handwritten signature in black ink, appearing to read 'Robert J. Patch', written over a horizontal line.

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RJP/psf
September 29, 2004

INFORMATION DISCLOSURE CITATION IN AN APPLICATION

(Use several sheets if necessary)

Attorney Docket No.:

8013-1139

Application No.:

09/944,186

Applicant:

YAMAGUCHI et al.

Filing Date:

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Group Art Unit:

2811

U.S. PATENT DOCUMENTS

Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing date (if appropriate)

FOREIGN PATENT DOCUMENTS

Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation	
						Yes	No

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

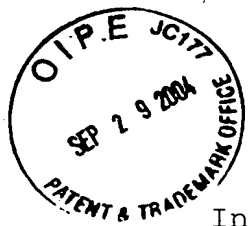
	DOMEN et al., "Optical gain in GaN Based Semiconductors", VERTICAL-CAVITY LASERS, TECHNOLOGIES FOR A GLOBAL INFORMATION INFRASTRUCTURE, WDM COMPONENTS TECHNOLOGY, ADVANCED SEMICONDUCTOR LASERS AND APPLICATIONS, GALLIUM NITRIDE MATERIALS, PROCESSING, AND DEVICES, 1997 DIGEST OF THE IEEE/LEOS SUMMER TOPICAL M, August 11, 1997, pp. 35-36, XP010243183
	DUXBURY et al., "Indium segregation in InGaN quantum-well structures", APPLIED PHYSICS LETTERS, AMERICAN INSTITUTE OF PHYSICS, NEW YORK, March 20, 2000, pp. 1600-1602, XP012024880
	BINET et al., "Optical pumping in nitride cavities with etched mirror facets", MATERIALS SCIENCE AND ENGINEERING B, ELSEVIER SEQUOIA, LAUSANNE, CH, December 18, 1997, pp. 183-187, XP004119130
	NAKAMURA, "Ingan-based blue laser diodes", IEEE JOURNAL OF SELECTED TOPICS IN QUANTUM ELECTRONICS, IEEE SERVICE CENTER, US, June 1, 1997, pp. 712-718, XP000727336
	FISCHER et al., "Direct imaging of the spectral emission characteristic of an InGaN/GaN-ultraviolet light-emitting diode by highly spectrally and spatially resolved electroluminescence and photoluminescence microscopy", APPLIED PHYSICS LETTERS, AMERICAN INSTITUTE OF PHYSICS, NEW YORK, US, November 29, 1999, pp. 3440-3442, XP012024140
	DOMEN et al., "Interwell inhomogeneity of carrier injection in InGaN/GaN/AlGaIn multiquantum well lasers", APPLIED PHYSICS LETTERS, AMERICAN INSTITUTE OF PHYSICS, NEW YORK, US, Vol. 73, No. 19, November 9, 1998, pp. 2775-2777, XP012021335

EXAMINER:

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.

* English language abstract provided for the Examiner's convenience



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PETITION UNDER 37 CFR 1.97(d)(2)(ii)

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

Applicants hereby request consideration of the Information Disclosure Statement filed under even date herewith.

Please charge the requisite 37 C.F.R. 1.17(p) fee of \$180.00 to Deposit Account No. 25-0120.

Respectfully submitted,

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